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Attorney's Docket No. 42P15685

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Scott A. Hareland, et al.

Application No.: 10/607,769

Filed: June 27, 2003

For: Nonplanar Semiconductor Device with  
Partially or Fully Wrapped Around Gate  
Electrode and Methods of Fabrication

Examiner: Unassigned

Art Unit: 2812

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
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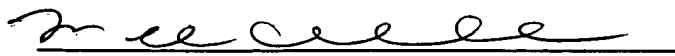
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If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: February 15, 2007

  
Michael A. Bernadicou  
Reg. No. 35,934

12400 Wilshire Blvd.  
Seventh Floor  
Los Angeles, CA 90025  
(408) 720-8300

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

**Complete if Known**

Application Number	10/607,769
Filing Date	June 27, 2003
First Named Inventor:	Scott A. Hareland
Art Unit	2812
Examiner Name	Such, Matthew W.
Attorney Docket No.:	42P15685

 Sheet **1** of **4**
**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)				
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# FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
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				Examiner Name	Such, Matthew W.
Sheet	3	of	4	Attorney Docket Number	42P15685
<b>NON PATENT LITERATURE DOCUMENTS</b>					
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T <sup>2</sup>
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